



# BUK7S2R5-40H

N-channel 40 V, 2.5 mOhm standard level MOSFET in LFPACK88

6 April 2021

Product data sheet

## 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPACK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

## 2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
  - 55 °C to +175 °C rating suitable for thermally demanding environments
- LFPACK88 package:
  - Designed for smaller footprint and improved power density over older wire bond packages such as D<sup>2</sup>PAK for today's space constrained high power automotive applications
  - Thin package and copper clip enables LFPACK88 to be highly efficient thermally
- LFPACK copper clip technology enabling improvements over wire bond packages by:
  - Increased maximum current capability and excellent current spreading
  - Improved  $R_{DSon}$
  - Low source inductance
  - Low thermal resistance  $R_{th}$
- LFPACK Gull Wing leads:
  - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
  - Reduced cell pitch and superjunction platform enables lower  $R_{DSon}$  in the same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight  $V_{GS(th)}$  limits enable easy paralleling of MOSFETs

## 3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

| Symbol    | Parameter               | Conditions                                                                |     | Min | Typ | Max | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                |     | -   | -   | 40  | V    |
| $I_D$     | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a> | [1] | -   | -   | 140 | A    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                          |     | -   | -   | 135 | W    |

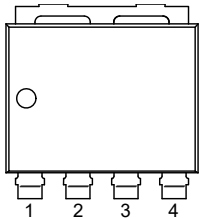
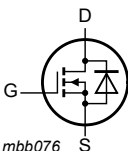
| Symbol                         | Parameter                        | Conditions                                                                                                                | Min  | Typ  | Max  | Unit |
|--------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| <b>Static characteristics</b>  |                                  |                                                                                                                           |      |      |      |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 11</a>               | 1.51 | 2.16 | 2.51 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                           |      |      |      |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 25\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -    | 7    | 14   | nC   |
| <b>Source-drain diode</b>      |                                  |                                                                                                                           |      |      |      |      |
| $Q_r$                          | recovered charge                 | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; <a href="#">[2]</a>                 | -    | 19.1 | -    | nC   |
| S                              | softness factor                  | $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 17</a>                                     | -    | 0.89 | -    |      |

[1] 140A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature

[2] includes capacitive recovery

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                          | Graphic symbol                                                                                     |
|-----|--------|-----------------------------------|-------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------|
| 1   | G      | gate                              |  <p>LFPAK88 (SOT1235)</p> |  <p>mbb076</p> |
| 2   | S      | Source                            |                                                                                                             |                                                                                                    |
| 3   | S      | Source                            |                                                                                                             |                                                                                                    |
| 4   | S      | Source                            |                                                                                                             |                                                                                                    |
| mb  | D      | mounting base; connected to drain |                                                                                                             |                                                                                                    |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package |                                                                                                         |         |
|--------------|---------|---------------------------------------------------------------------------------------------------------|---------|
|              | Name    | Description                                                                                             | Version |
| BUK7S2R5-40H | LFPAK88 | plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body | SOT1235 |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK7S2R5-40H | 7S2R540H     |

## 8. Limiting values

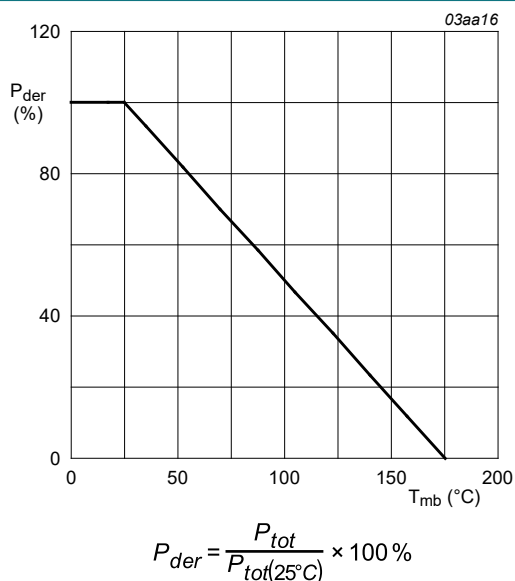
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

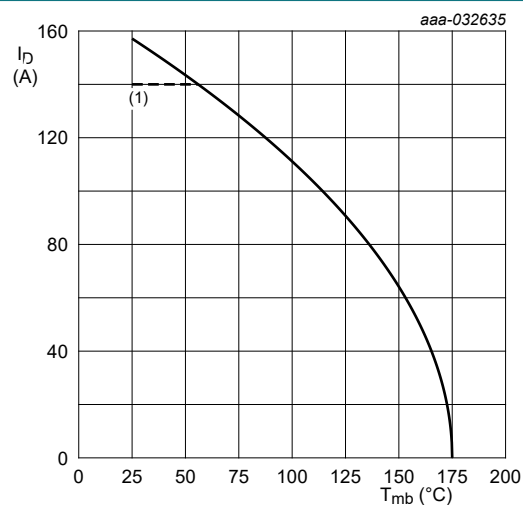
| Symbol   | Parameter            | Conditions                                                             | Min | Max | Unit |
|----------|----------------------|------------------------------------------------------------------------|-----|-----|------|
| $V_{DS}$ | drain-source voltage | $25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$ | -   | 40  | V    |

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                                      |         | Min | Max | Unit               |
|-----------------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|-----|--------------------|
| $V_{GS}$                    | gate-source voltage                          | DC; $T_j = 175\text{ }^{\circ}\text{C}$                                                                                                                                         |         | -10 | 20  | V                  |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 1                                                                                                                                  |         | -   | 135 | W                  |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 2                                                                                                         | [1]     | -   | 140 | A                  |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 3                                                                                       |         | -   | 629 | A                  |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                                                 |         | -55 | 175 | $^{\circ}\text{C}$ |
| $T_j$                       | junction temperature                         |                                                                                                                                                                                 |         | -55 | 175 | $^{\circ}\text{C}$ |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                                                 |         |     |     |                    |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ }^{\circ}\text{C}$                                                                                                                                           | [2]     | -   | 135 | A                  |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$                                                                                                |         | -   | 629 | A                  |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                                 |         |     |     |                    |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 96\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; unclamped; Fig. 4 | [3] [4] | -   | 80  | mJ                 |
| $I_{AS}$                    | non-repetitive avalanche current             | $V_{sup} = 40\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $R_{GS} = 50\text{ }\Omega$                                              | [5]     | -   | 96  | A                  |

- [1] 140A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] 135A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}$ .
- [4] Refer to application note AN10273 for further information.
- [5] Protected by 100% test.



**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



$V_{GS} \geq 10\text{ V}$

(1) 140A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2. Continuous drain current as a function of mounting base temperature**

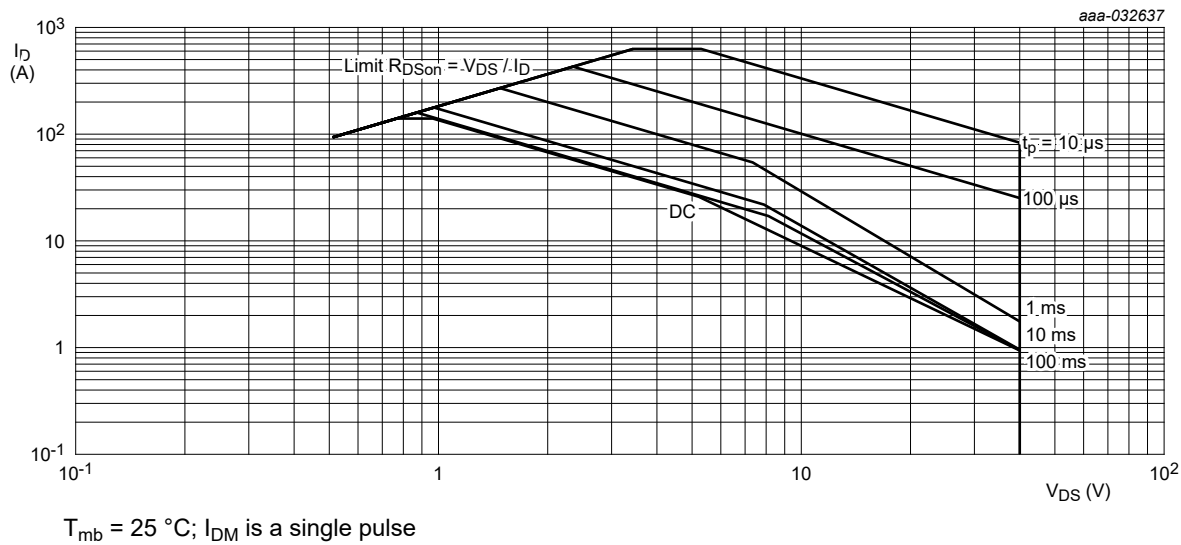
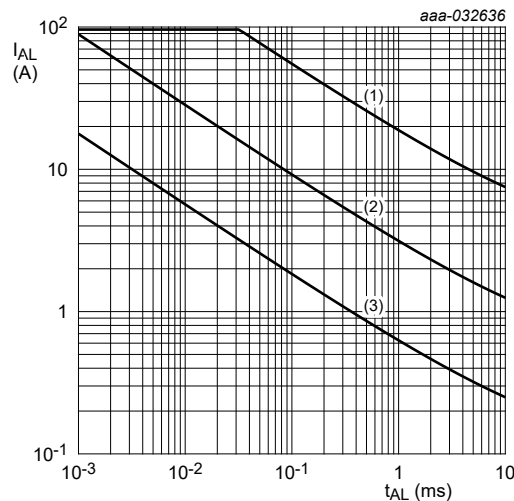


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j\text{ (init)}} = 25\text{ }^{\circ}\text{C}$ ; (2)  $T_{j\text{ (init)}} = 150\text{ }^{\circ}\text{C}$ ; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | 0.97 | 1.11 | K/W  |

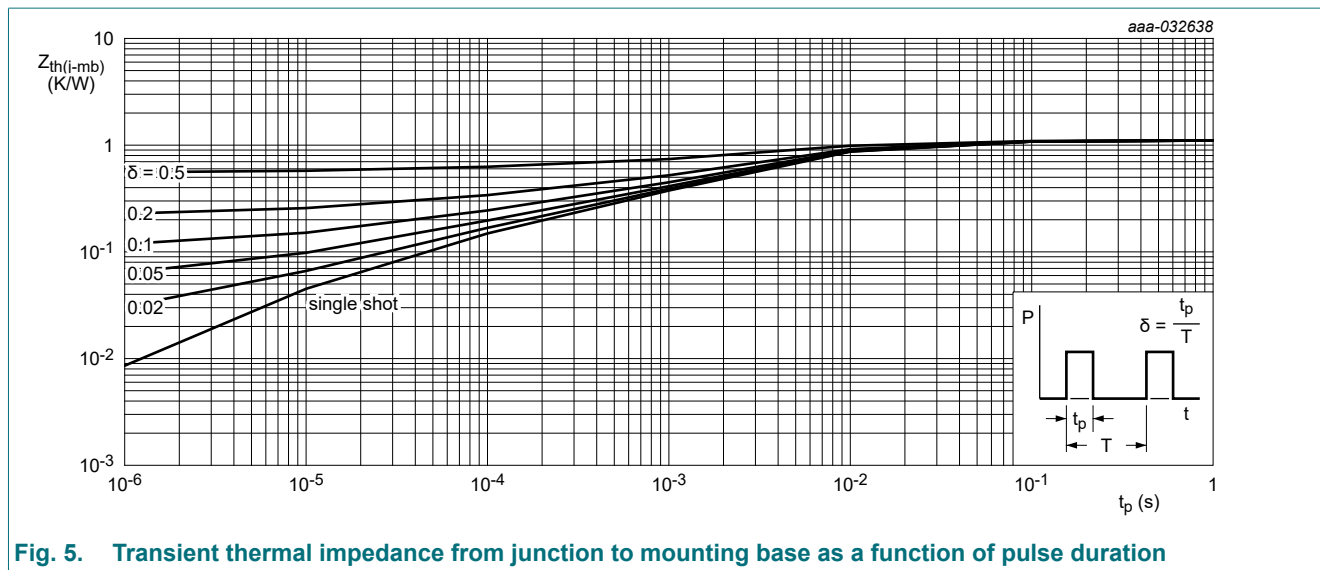


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

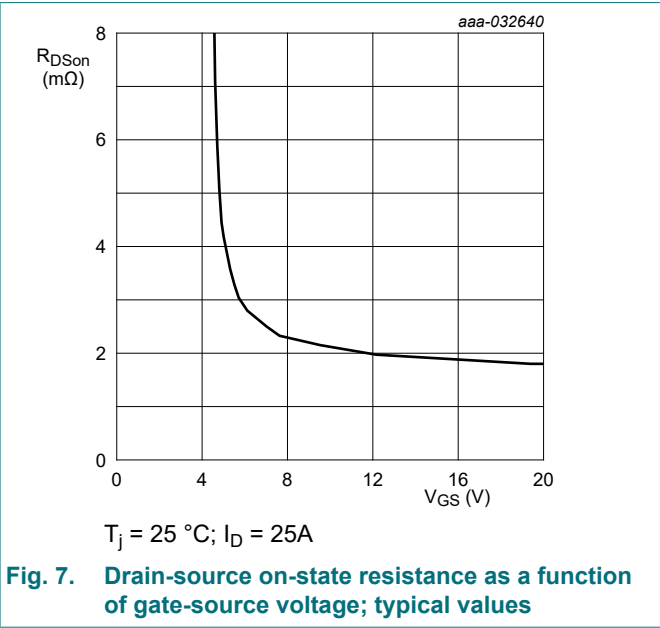
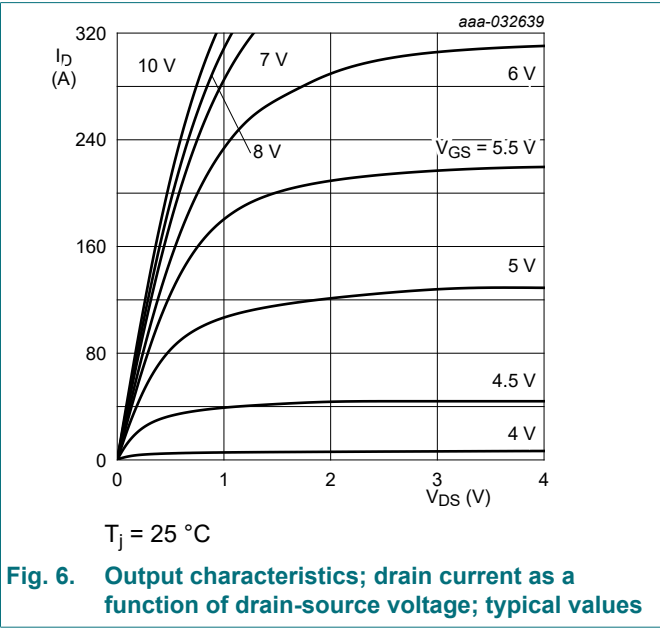
## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                        | Conditions                                                                                               | Min  | Typ   | Max  | Unit       |
|--------------------------------|----------------------------------|----------------------------------------------------------------------------------------------------------|------|-------|------|------------|
| <b>Static characteristics</b>  |                                  |                                                                                                          |      |       |      |            |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_J = 25^\circ C$                                                  | 40   | 43    | -    | V          |
|                                |                                  | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_J = -40^\circ C$                                                 | -    | 40.5  | -    | V          |
|                                |                                  | $I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_J = -55^\circ C$                                                 | 36   | 40    | -    | V          |
| $V_{GS(th)}$                   | gate-source threshold voltage    | $I_D = 1 mA$ ; $V_{DS} = V_{GS}$ ; $T_J = 25^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a> | 2.4  | 3     | 3.6  | V          |
|                                |                                  | $I_D = 1 mA$ ; $V_{DS} = V_{GS}$ ; $T_J = -55^\circ C$ ; <a href="#">Fig. 10</a>                         | -    | -     | 4.3  | V          |
|                                |                                  | $I_D = 1 mA$ ; $V_{DS} = V_{GS}$ ; $T_J = 175^\circ C$ ; <a href="#">Fig. 10</a>                         | 1    | -     | -    | V          |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = 40 V$ ; $V_{GS} = 0 V$ ; $T_J = 25^\circ C$                                                    | -    | 0.027 | 1    | $\mu A$    |
|                                |                                  | $V_{DS} = 16 V$ ; $V_{GS} = 0 V$ ; $T_J = 125^\circ C$                                                   | -    | 0.7   | 10   | $\mu A$    |
|                                |                                  | $V_{DS} = 40 V$ ; $V_{GS} = 0 V$ ; $T_J = 175^\circ C$                                                   | -    | 82    | 500  | $\mu A$    |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 20 V$ ; $V_{DS} = 0 V$ ; $T_J = 25^\circ C$                                                    | -    | 2     | 100  | nA         |
|                                |                                  | $V_{GS} = -10 V$ ; $V_{DS} = 0 V$ ; $T_J = 25^\circ C$                                                   | -    | 2     | 100  | nA         |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10 V$ ; $I_D = 25 A$ ; $T_J = 25^\circ C$ ; <a href="#">Fig. 11</a>                            | 1.51 | 2.16  | 2.51 | m $\Omega$ |
|                                |                                  | $V_{GS} = 10 V$ ; $I_D = 25 A$ ; $T_J = 105^\circ C$ ; <a href="#">Fig. 12</a>                           | 2.14 | 3.32  | 3.99 | m $\Omega$ |
|                                |                                  | $V_{GS} = 10 V$ ; $I_D = 25 A$ ; $T_J = 125^\circ C$ ; <a href="#">Fig. 12</a>                           | 2.37 | 3.64  | 4.39 | m $\Omega$ |
|                                |                                  | $V_{GS} = 10 V$ ; $I_D = 25 A$ ; $T_J = 175^\circ C$ ; <a href="#">Fig. 12</a>                           | 2.97 | 4.52  | 5.47 | m $\Omega$ |
| $R_G$                          | gate resistance                  | $f = 1 MHz$ ; $T_J = 25^\circ C$                                                                         | 0.31 | 0.76  | 1.91 | $\Omega$   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                          |      |       |      |            |
| $Q_{G(tot)}$                   | total gate charge                | $I_D = 25 A$ ; $V_{DS} = 32 V$ ; $V_{GS} = 10 V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>     | -    | 38    | 54   | nC         |
| $Q_{GS}$                       | gate-source charge               |                                                                                                          | -    | 11    | 16   | nC         |
| $Q_{GD}$                       | gate-drain charge                |                                                                                                          | -    | 7     | 14   | nC         |

| Symbol              | Parameter                    | Conditions                                                                                                                                                |     | Min | Typ  | Max  | Unit |
|---------------------|------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|------|
| C <sub>iss</sub>    | input capacitance            | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;<br>T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>                                              |     | -   | 2709 | 3793 | pF   |
| C <sub>oss</sub>    | output capacitance           |                                                                                                                                                           |     | -   | 729  | 1021 | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance |                                                                                                                                                           |     | -   | 127  | 279  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time           | V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V;<br>R <sub>G(ext)</sub> = 5 Ω                                                      |     | -   | 10   | -    | ns   |
| t <sub>r</sub>      | rise time                    |                                                                                                                                                           |     | -   | 8.5  | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time          |                                                                                                                                                           |     | -   | 22   | -    | ns   |
| t <sub>f</sub>      | fall time                    |                                                                                                                                                           |     | -   | 11   | -    | ns   |
| Source-drain diode  |                              |                                                                                                                                                           |     |     |      |      |      |
| V <sub>SD</sub>     | source-drain voltage         | I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>                                                             |     | -   | 0.79 | 1    | V    |
| t <sub>rr</sub>     | reverse recovery time        | I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V;<br>V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a> |     | -   | 30.1 | -    | ns   |
| Q <sub>r</sub>      | recovered charge             |                                                                                                                                                           | [1] | -   | 19.1 | -    | nC   |
| S                   | softness factor              |                                                                                                                                                           |     | -   | 0.89 | -    |      |
|                     |                              | I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -500 A/μs; V <sub>GS</sub> = 0 V;<br>V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a> |     | -   | 0.67 | -    |      |

[1] includes capacitive recovery



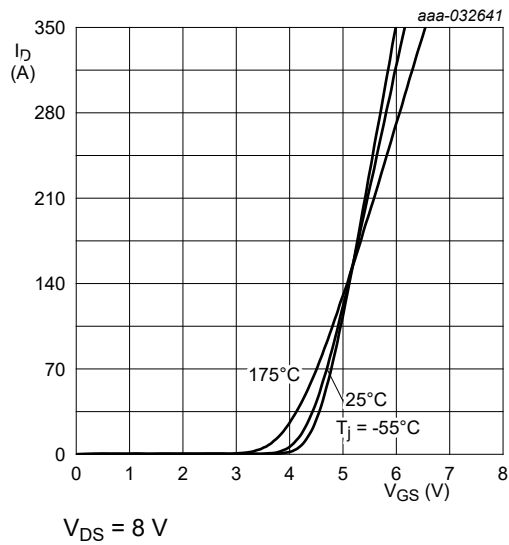


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

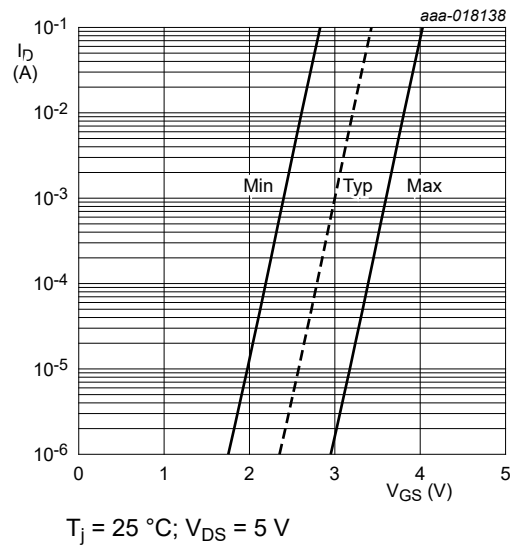


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

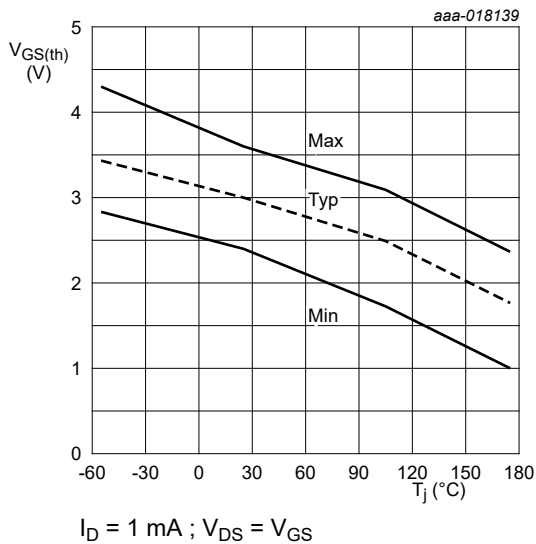


Fig. 10. Gate-source threshold voltage as a function of junction temperature

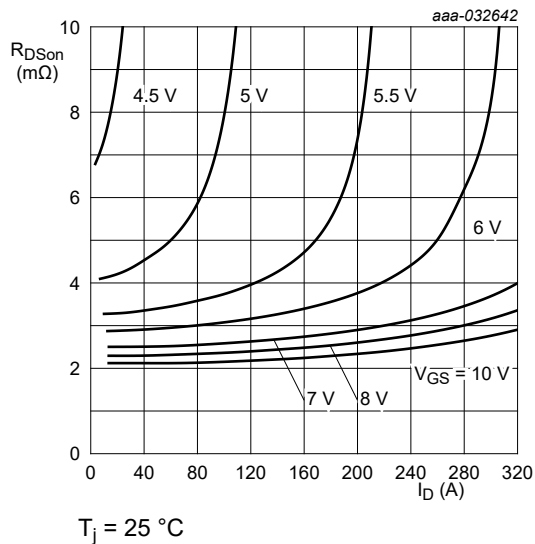


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

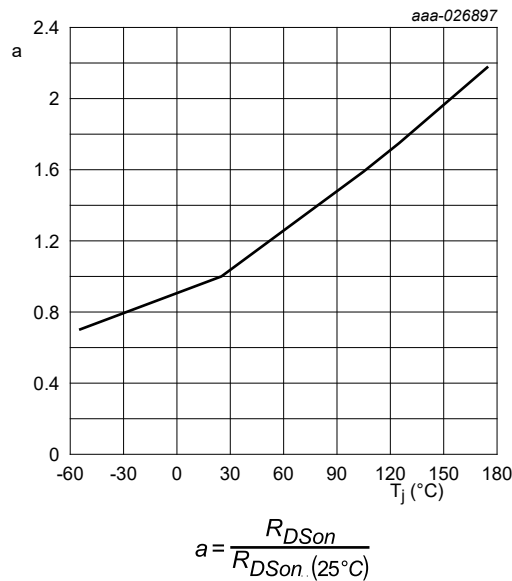


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

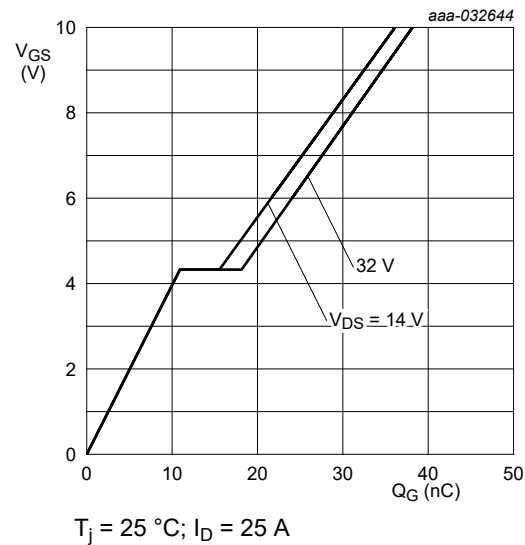


Fig. 13. Gate-source voltage as a function of gate charge; typical values

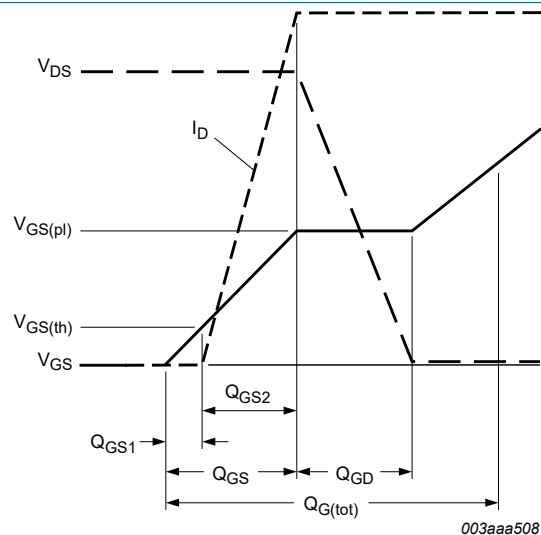


Fig. 14. Gate charge waveform definitions

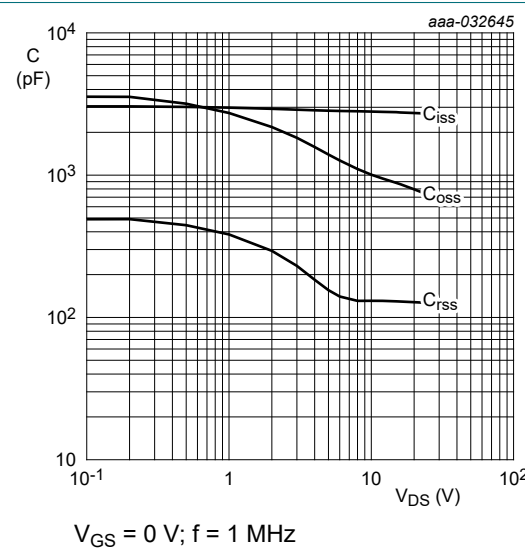
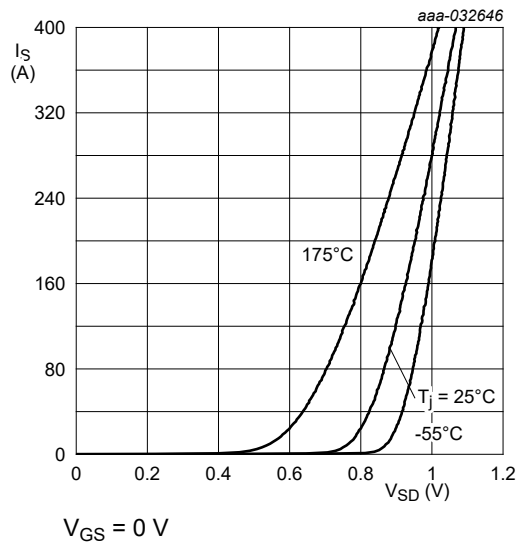
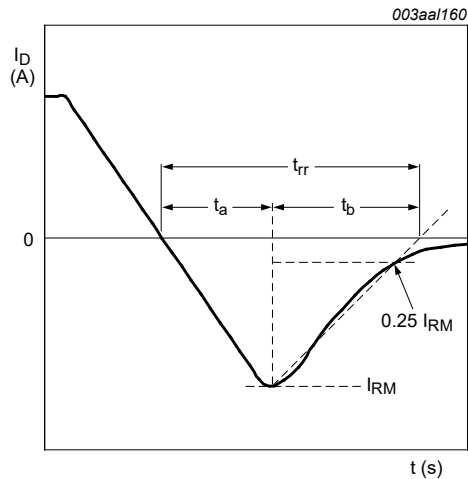


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





**Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



**Fig. 17. Reverse recovery timing definition**

11. Package outline

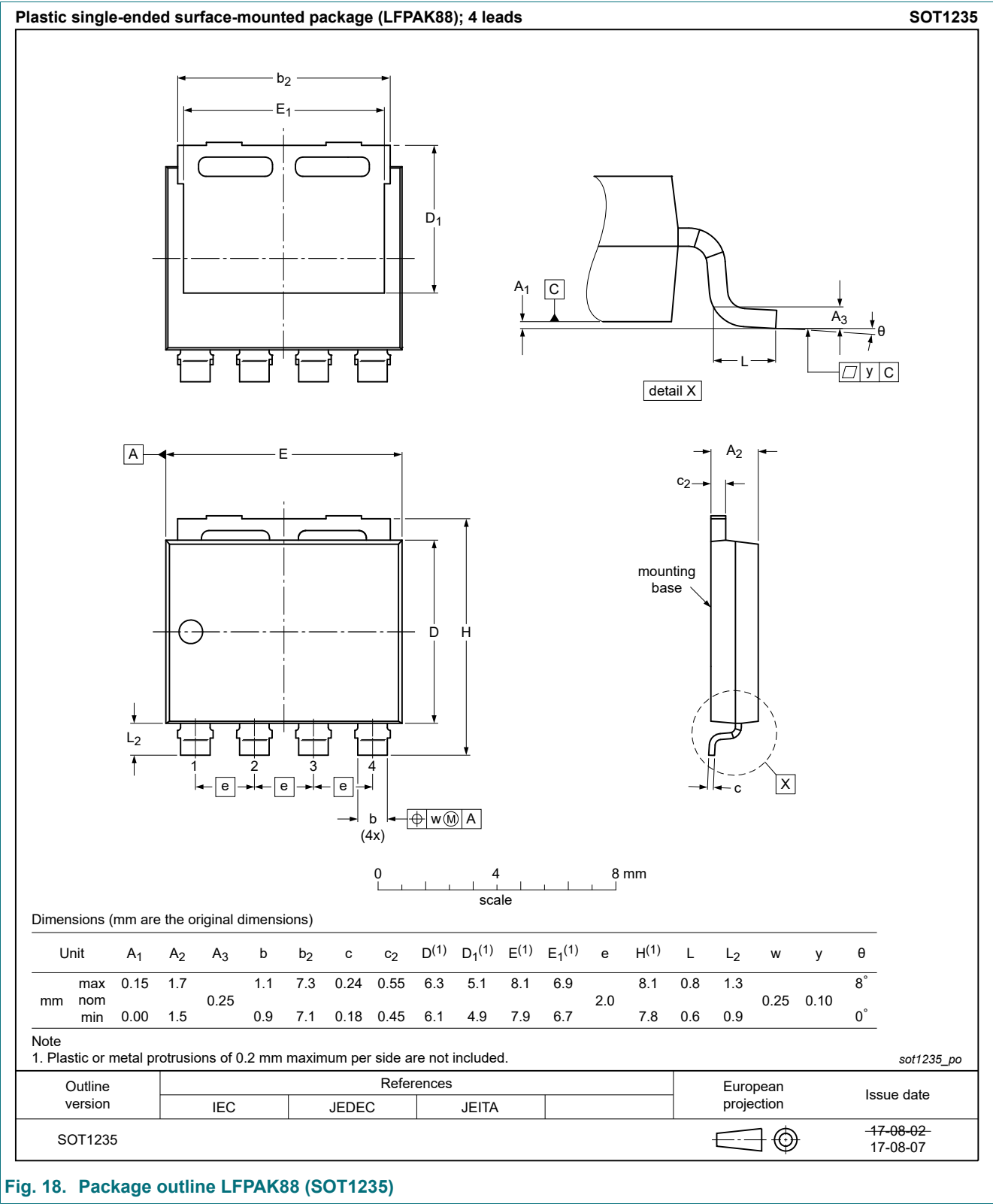
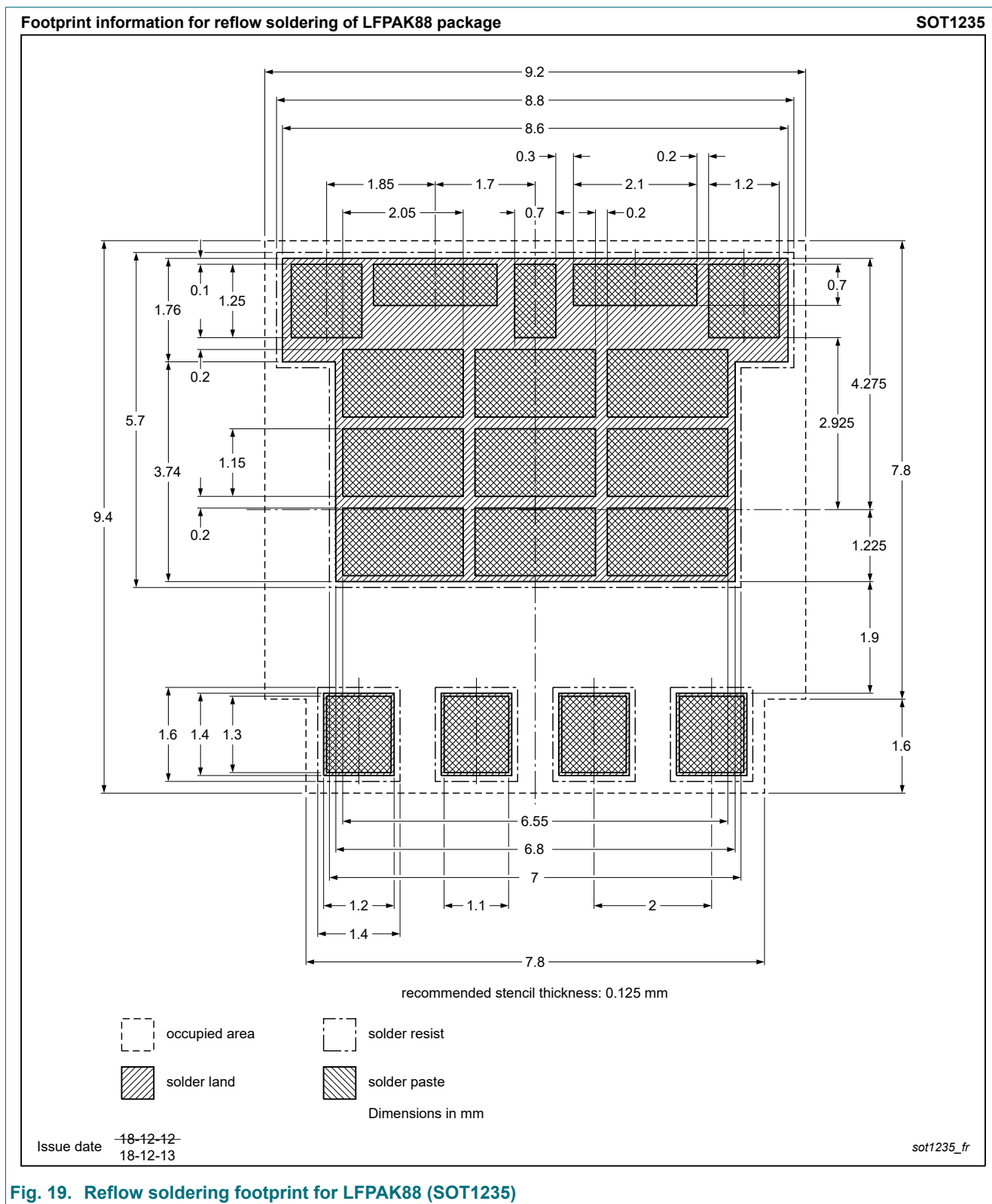


Fig. 18. Package outline LPAK88 (SOT1235)

## 12. Soldering



**Fig. 19. Reflow soldering footprint for LPAK88 (SOT1235)**

## 13. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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